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ON Semiconductor®

# FQD4P40

## P-Channel QFET® MOSFET

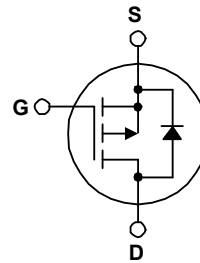
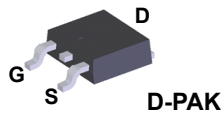
-400 V, -2.7 A, 3.1 Ω

### Features

- -2.7 A, -400 V,  $R_{DS(on)} = 3.1 \Omega$  (Max.) @  $V_{GS} = -10 V$ ,  $I_D = -1.35 A$
- Low Gate Charge (Typ. 18 nC)
- Low Crss (Typ. 11 pF)
- 100% Avalanche Tested

### Description

These P-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp ballast based on complimentary half bridge.



### Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

| Symbol         | Parameter   | FQD4P40TM   | Unit          |
|----------------|---|-------------|---------------|
| $V_{DSS}$      | Drain-Source Voltage  | -400        | V             |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ C$ )<br>- Continuous ( $T_C = 100^\circ C$ ) | -2.7        | A             |
|                |   | -1.71       | A             |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)   | -10.8       | A             |
| $V_{GSS}$      | Gate-Source Voltage   | $\pm 30$    | V             |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)   | 260         | mJ            |
| $I_{AR}$       | Avalanche Current (Note 1)  | -2.7        | A             |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)  | 5.0         | mJ            |
| dv/dt          | Peak Diode Recovery dv/dt (Note 3)  | -4.5        | V/ns          |
| $P_D$          | Power Dissipation ( $T_A = 25^\circ C$ ) *  | 2.5         | W             |
|                | Power Dissipation ( $T_C = 25^\circ C$ )  | 50          | W             |
|                | - Derate above $25^\circ C$   | 0.4         | W/ $^\circ C$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range   | -55 to +150 | $^\circ C$    |
| $T_L$          | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds             | 300         | $^\circ C$    |

### Thermal Characteristics

| Symbol          | Parameter   | FQD4P40TM | Unit         |
|-----------------|---|-----------|--------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max.  | 2.5       | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.            | 110       |              |
|                 | Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max. | 50        |              |

FQD4P40 — P-Channel QFET® MOSFET

## Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity   |
|-------------|----------|---------|----------------|-----------|------------|------------|
| FQD4P40TM   | FQD4P40  | DPAK    | Tape and Reel  | 330 mm    | 16 mm      | 2500 units |

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

### Off Characteristics

|                                |   |  |      |      |      |                           |
|--------------------------------|---|--|------|------|------|---------------------------|
| $BV_{DSS}$                     | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$               | -400 | --   | --   | V                         |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$ | --   | 0.36 | --   | $\text{V}/^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = -400\text{ V}, V_{GS} = 0\text{ V}$                | --   | --   | -1   | $\mu\text{A}$             |
|                                |   | $V_{DS} = -320\text{ V}, T_C = 125^\circ\text{C}$            | --   | --   | -10  | $\mu\text{A}$             |
| $I_{GSSF}$                     | Gate-Body Leakage Current, Forward        | $V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$                 | --   | --   | -100 | nA                        |
| $I_{GSSR}$                     | Gate-Body Leakage Current, Reverse        | $V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$                  | --   | --   | 100  | nA                        |

### On Characteristics

|              |                                   |   |      |      |      |          |
|--------------|-----------------------------------|---|------|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$    | -3.0 | --   | -5.0 | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = -10\text{ V}, I_D = -1.35\text{ A}$ | --   | 2.44 | 3.1  | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = -50\text{ V}, I_D = -1.35\text{ A}$ | --   | 2.5  | --   | S        |

### Dynamic Characteristics

|            |                              |   |    |     |     |    |
|------------|------------------------------|---|----|-----|-----|----|
| $C_{iss}$  | Input Capacitance            | $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ | -- | 520 | 680 | pF |
| $C_{oss}$  | Output Capacitance           |   | -- | 80  | 105 | pF |
| $C_{riss}$ | Reverse Transfer Capacitance |   | -- | 11  | 15  | pF |

### Switching Characteristics

|              |                     |   |          |    |     |    |    |
|--------------|---------------------|---|----------|----|-----|----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = -200\text{ V}, I_D = -3.5\text{ A},$<br>$R_G = 25\ \Omega$      | --       | 13 | 35  | ns |    |
| $t_r$        | Turn-On Rise Time   |   | --       | 55 | 120 | ns |    |
| $t_{d(off)}$ | Turn-Off Delay Time |   | (Note 4) | -- | 35  | 80 | ns |
| $t_f$        | Turn-Off Fall Time  |   | (Note 4) | -- | 37  | 85 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = -320\text{ V}, I_D = -3.5\text{ A},$<br>$V_{GS} = -10\text{ V}$ | --       | 18 | 23  | nC |    |
| $Q_{gs}$     | Gate-Source Charge  |   | (Note 4) | -- | 3.8 | -- | nC |
| $Q_{gd}$     | Gate-Drain Charge   |   | (Note 4) | -- | 9.4 | -- | nC |

### Drain-Source Diode Characteristics and Maximum Ratings

|          |   |   |    |       |      |               |
|----------|---|---|----|-------|------|---------------|
| $I_S$    | Maximum Continuous Drain-Source Diode Forward Current | --  | -- | -2.7  | A    |               |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current     | --  | -- | -10.8 | A    |               |
| $V_{SD}$ | Drain-Source Diode Forward Voltage                    | $V_{GS} = 0\text{ V}, I_S = -2.7\text{ A}$  | -- | --    | -5.0 | V             |
| $t_{rr}$ | Reverse Recovery Time                                 | $V_{GS} = 0\text{ V}, I_S = -3.5\text{ A},$<br>$di_F / dt = 100\text{ A}/\mu\text{s}$ | -- | 260   | --   | ns            |
| $Q_{rr}$ | Reverse Recovery Charge                               |   | -- | 1.4   | --   | $\mu\text{C}$ |

#### Notes:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2.  $L = 62\text{ mH}, I_{AS} = -2.7\text{ A}, V_{DD} = -50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq -3.5\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

## Typical Characteristics

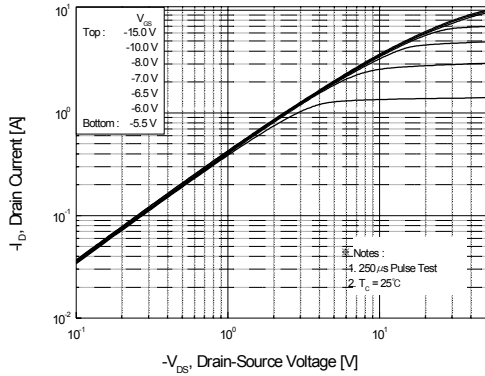


Figure 1. On-Region Characteristics

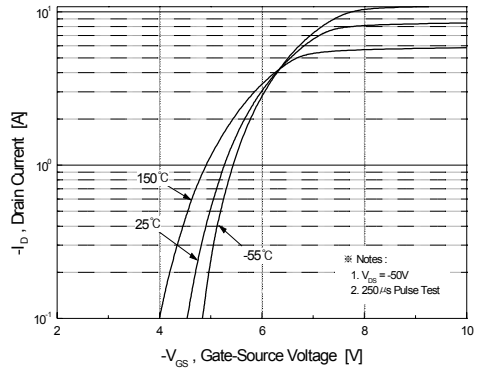


Figure 2. Transfer Characteristics

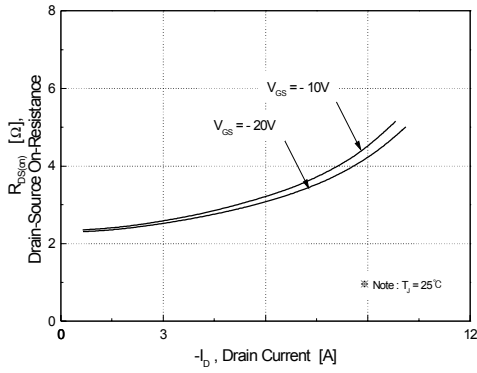


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

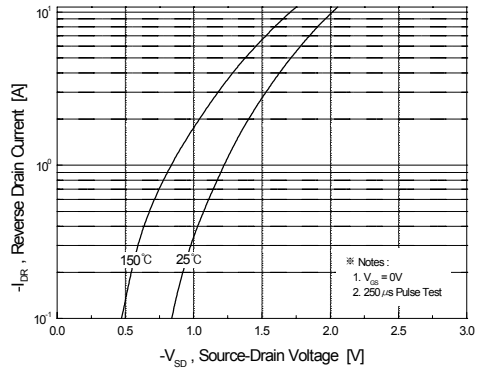


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

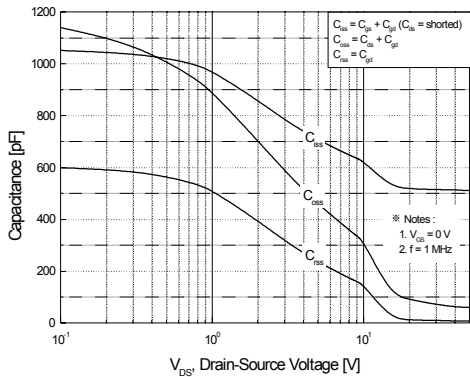


Figure 5. Capacitance Characteristics

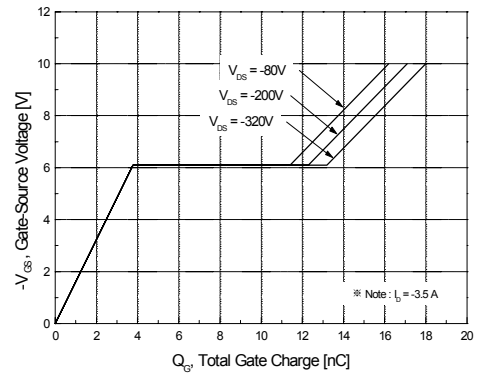
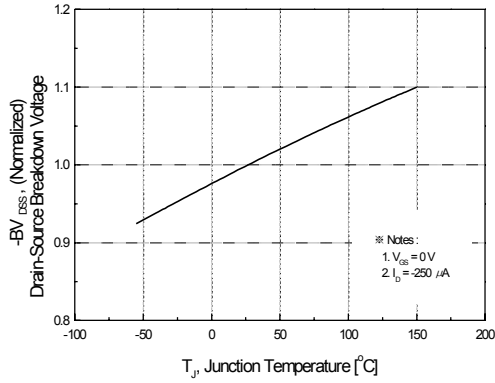
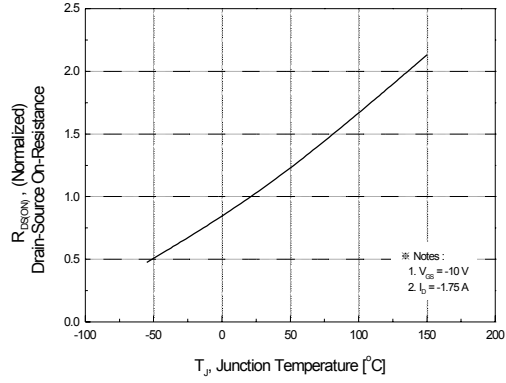


Figure 6. Gate Charge Characteristics

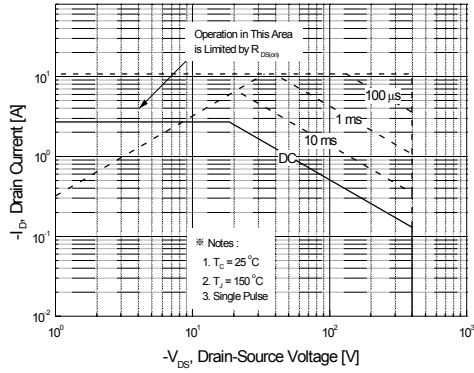
**Typical Characteristics** (Continued)



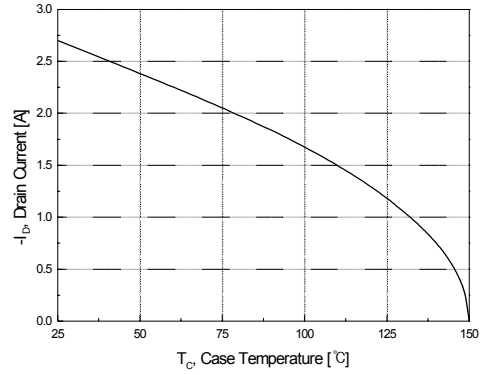
**Figure 7. Breakdown Voltage Variation vs. Temperature**



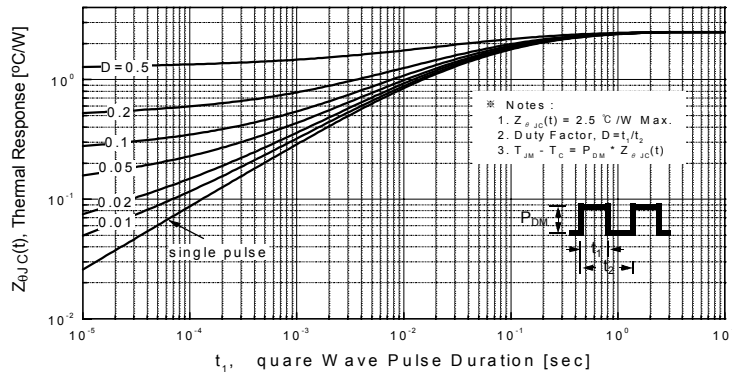
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

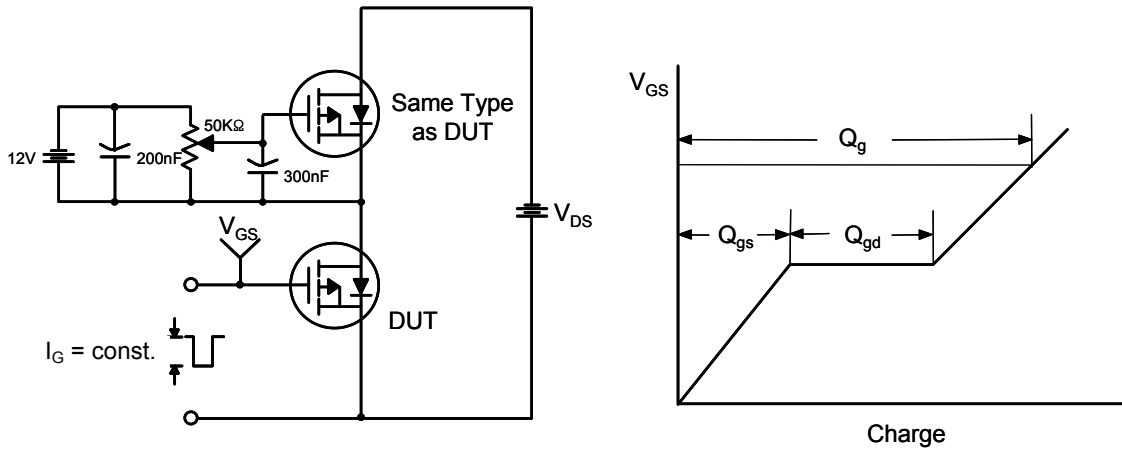


Figure 12. Gate Charge Test Circuit & Waveform

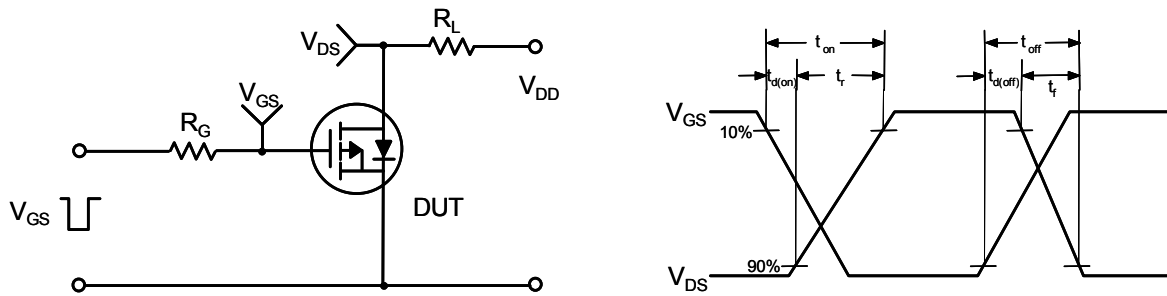


Figure 13. Resistive Switching Test Circuit & Waveforms

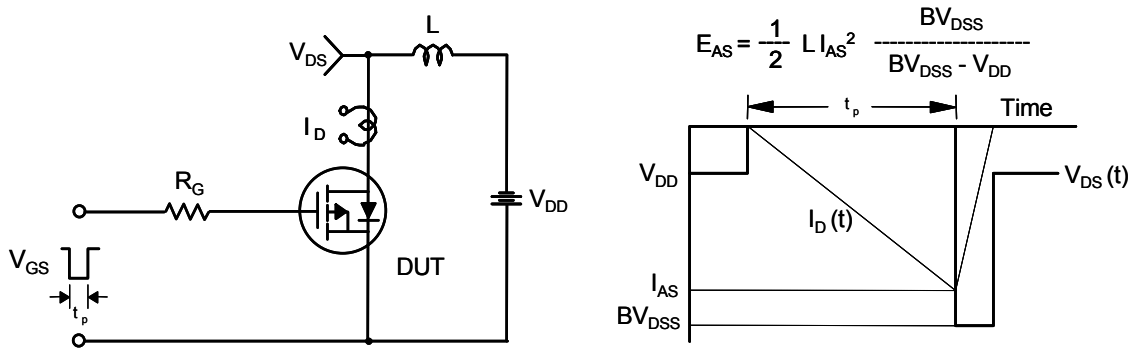


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

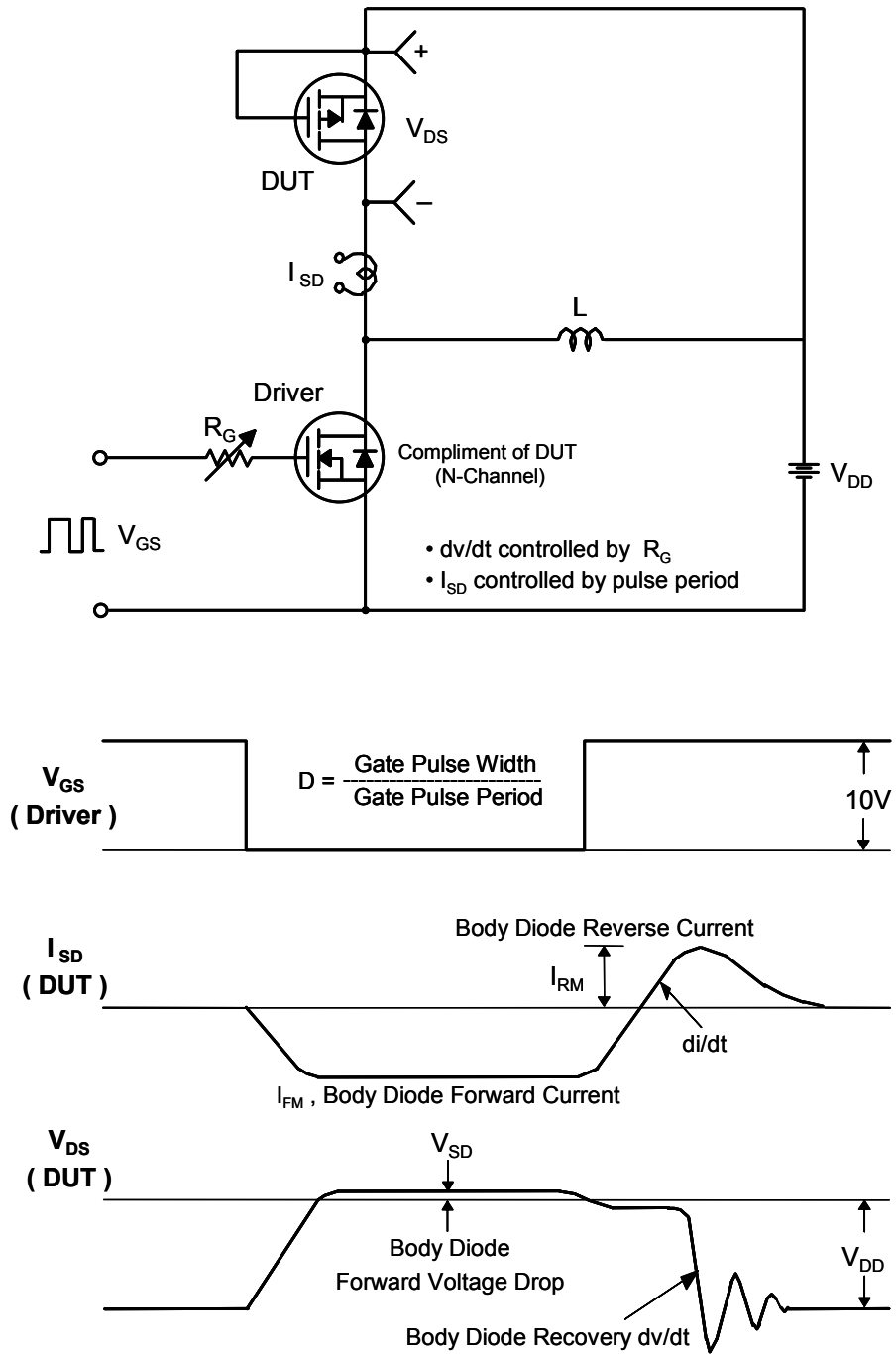
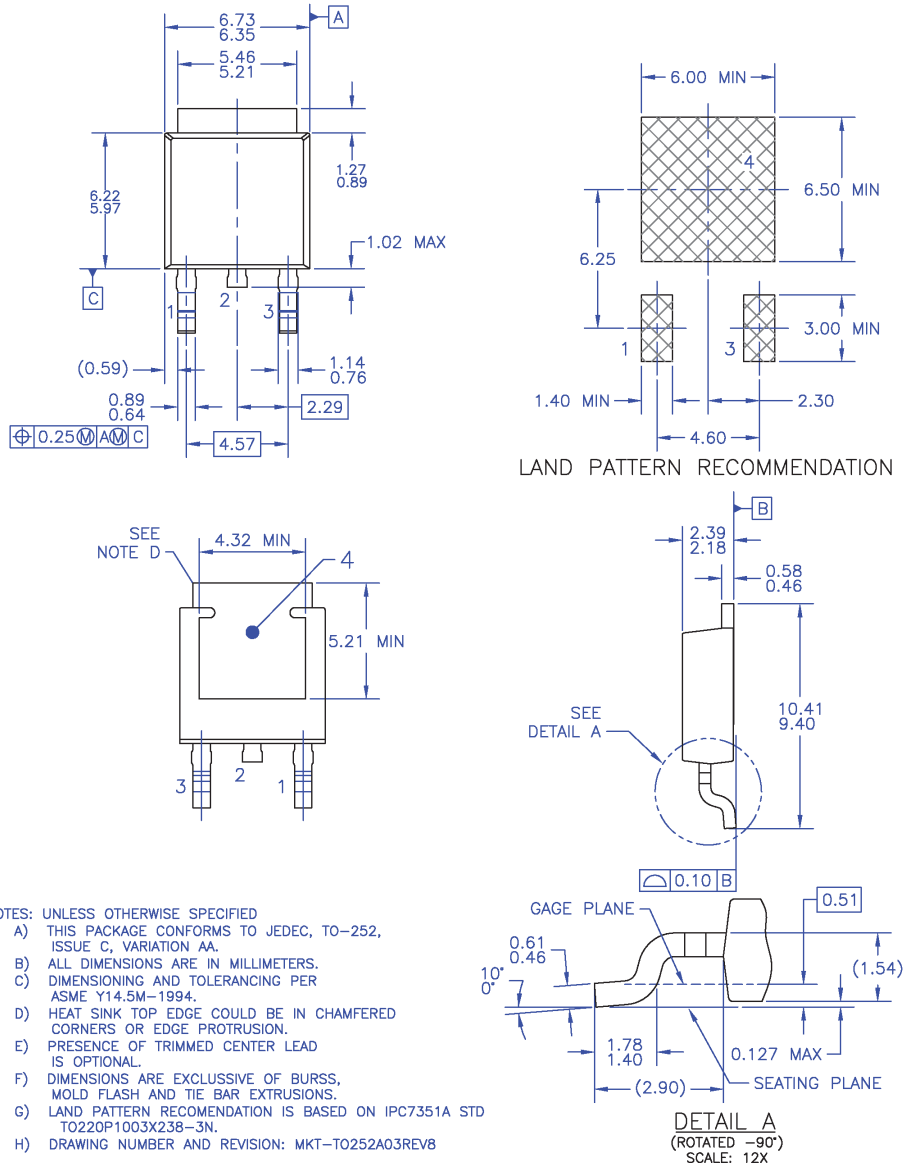


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

## Mechanical Dimensions



**Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB**

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